DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D T_A = +25°C
30V	1.2Ω @ V_{GS} = 4.5V	0.68A
	1.5Ω @ V_{GS} = 2.5V	0.61A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Features and Benefits

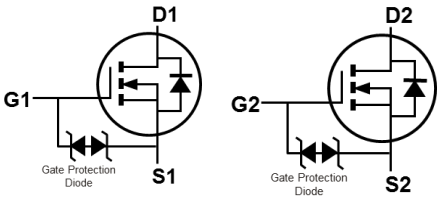
- Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at https://www.diodes.com/products/automotive/automotive-products/.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/**

Mechanical Data

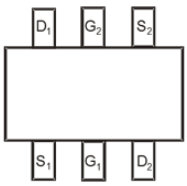
- Package: SOT563
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.006 grams (Approximate)

SOT563

Top View



Internal Schematic



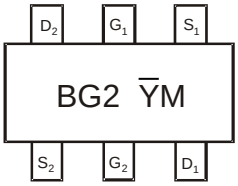
Top View
Pin Out

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN32D0LV-7	SOT563	3000	Tape & Reel
DMN32D0LV-13	SOT563	10000	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



BG2 = Product Type Marking Code
$\overline{Y}$M = Date Code Marking
$\overline{Y}$ = Year (ex: J = 2022)
M = Month (ex: 9 = September)

Date Code Key

Year	2014	….	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	B	….	J	K	L	M	N	O	P	R	S	T

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V_{DSS}	30	V
Gate-Source Voltage	Continuous	V_{GSS}	±10	V
Drain Current (Note 5)	Continuous	I_D	0.68	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	480	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	261	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Note: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	10	µA	V_{GS} = ±10V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.6	—	1.2	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	— — —	— — —	1.2 1.5 2.2	Ω	V_{GS} = 4.0V, I_D = 100mA V_{GS} = 2.5V, I_D = 20mA V_{GS} = 1.8V, I_D = 20mA
Source-Drain Diode Forward Voltage	V_{SD}	—	—	1.4	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	44.8	—	pF	V_{DS} = 15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	4.6	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.5	—	pF	
Total Gate Charge	Q_g	—	0.62	—	nC	V_{GS} = 4.5V, V_{DS} = 15V I_D = 350mA
Gate-Source Charge	Q_{gs}	—	0.12	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.24	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.41	—	ns	V_{DD} = 20V, R_L = 250Ω V_{GEN} = 4.5V, R_{GEN} = 6Ω
Turn-On Rise Time	t_R	—	2.45	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	19.0	—	ns	
Turn-Off Fall Time	t_F	—	7.86	—	ns	

Notes: 6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

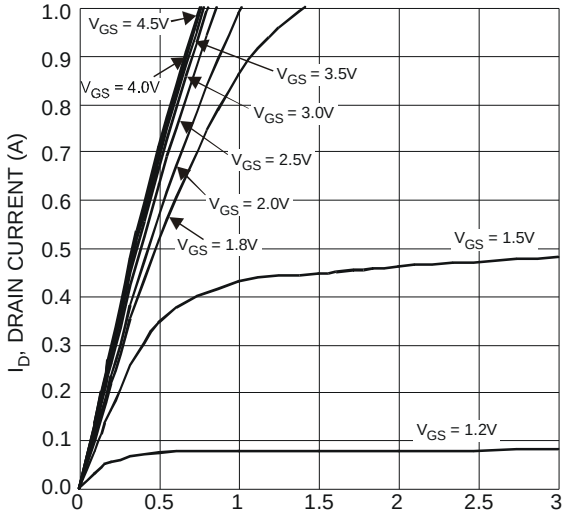


Figure 1 Typical Output Characteristics

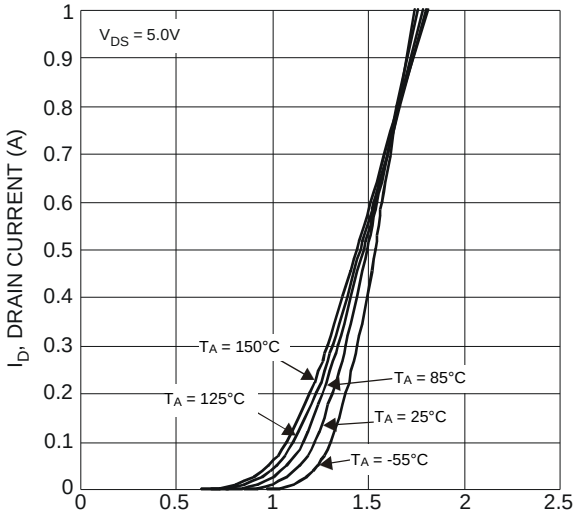


Figure 2 Typical Transfer Characteristics

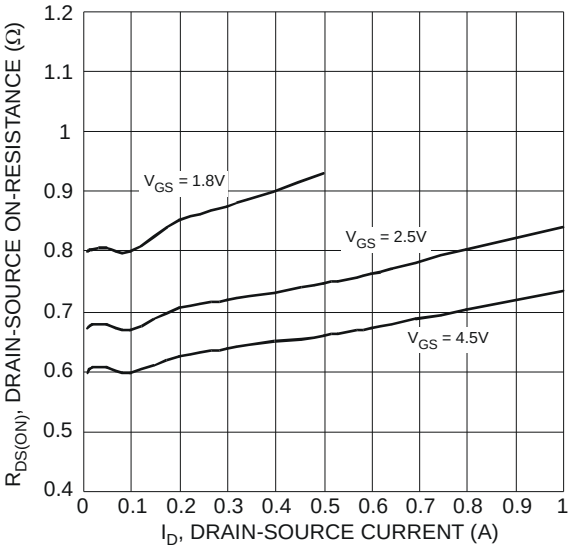


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

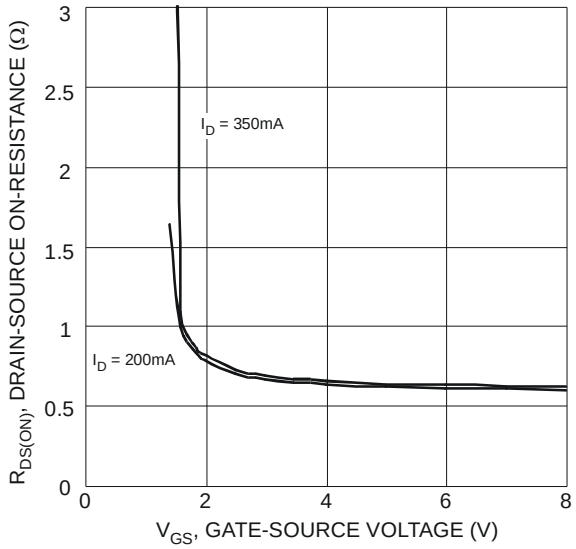


Figure 4 Typical Transfer Characteristics

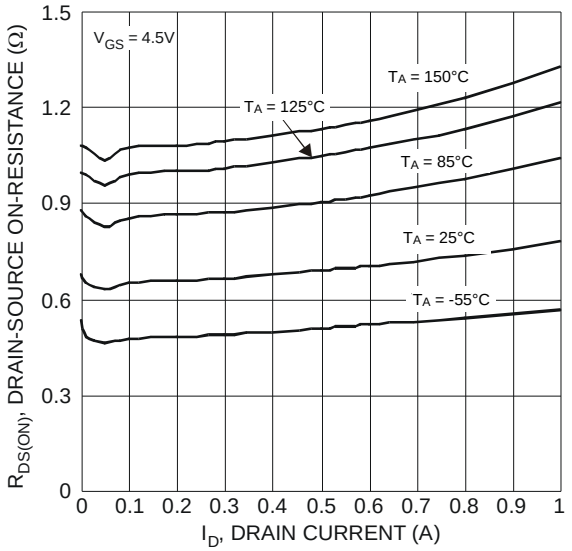


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

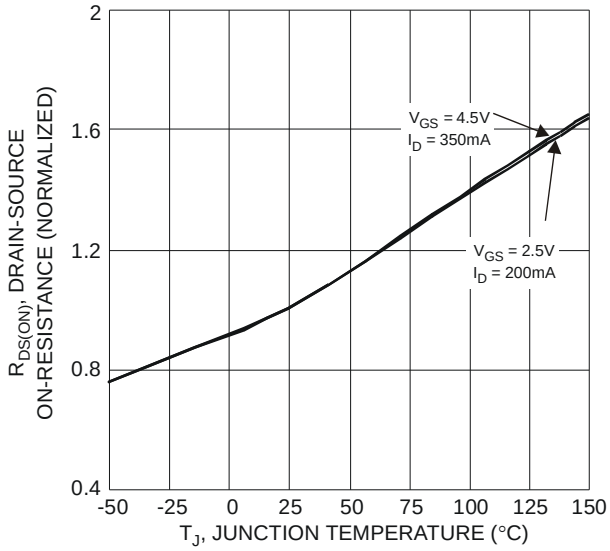


Figure 6 On-Resistance Variation with Temperature

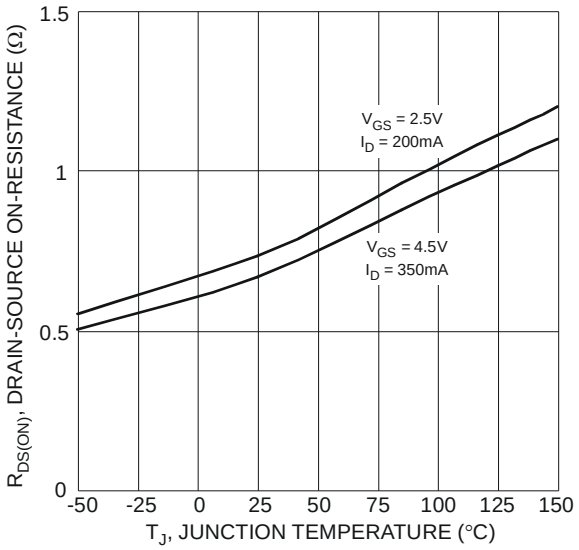


Figure 7 On-Resistance Variation with Temperature

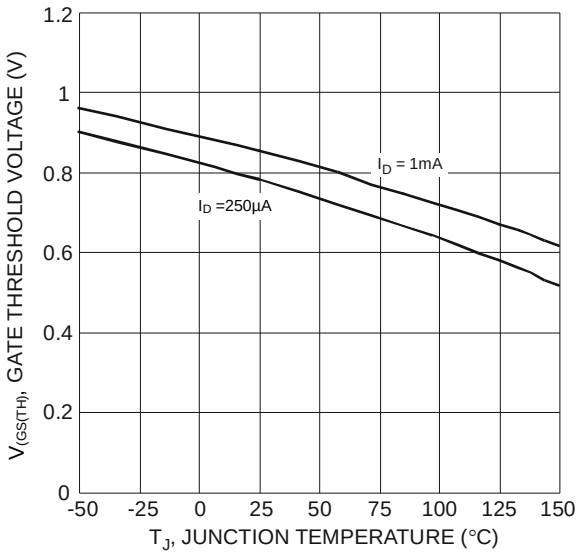


Figure 8 Gate Threshold Variation vs. Junction Temperature

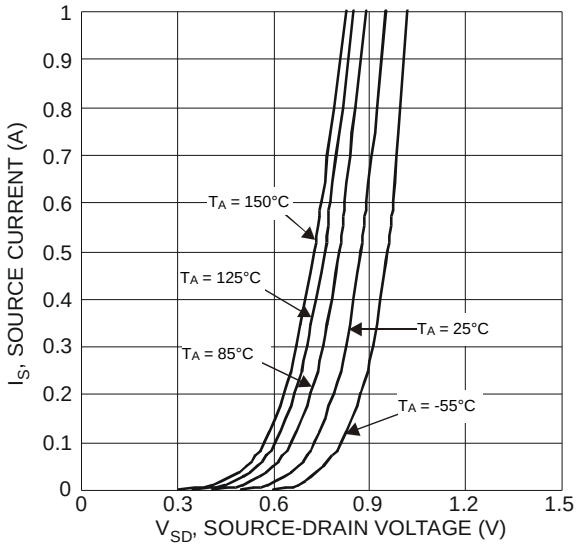


Figure 9 Diode Forward Voltage vs. Current

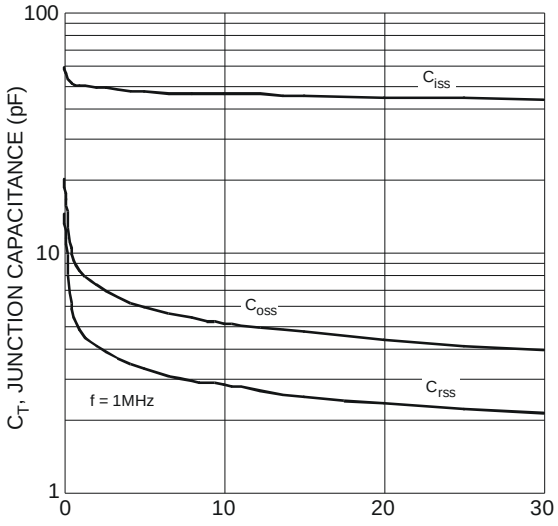


Figure 10 Typical Junction Capacitance

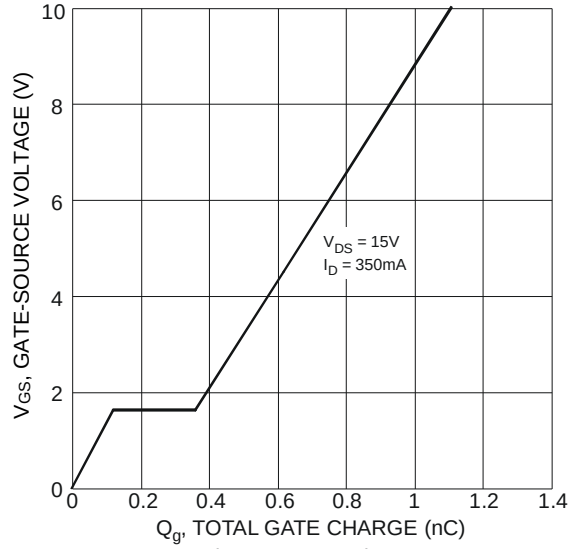


Figure 11 Gate Charge

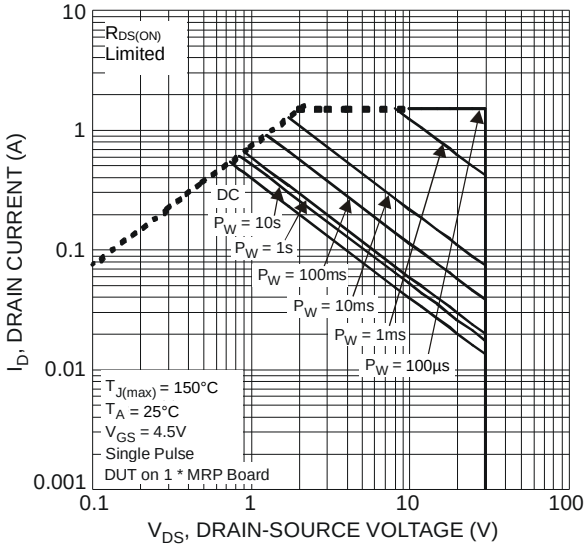


Figure 12 SOA, Safe Operation Area

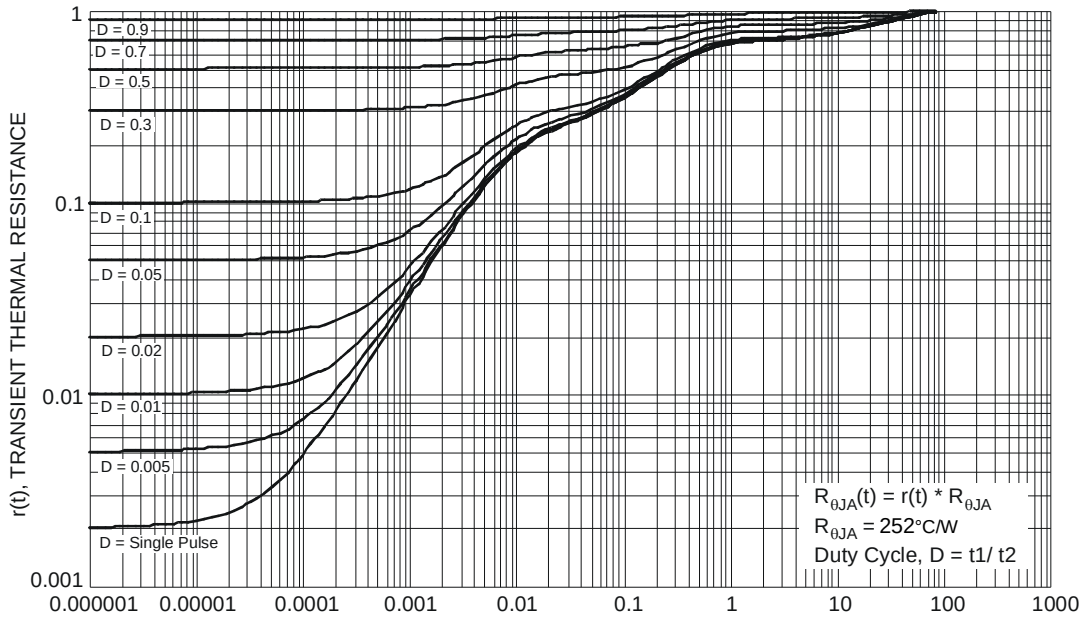


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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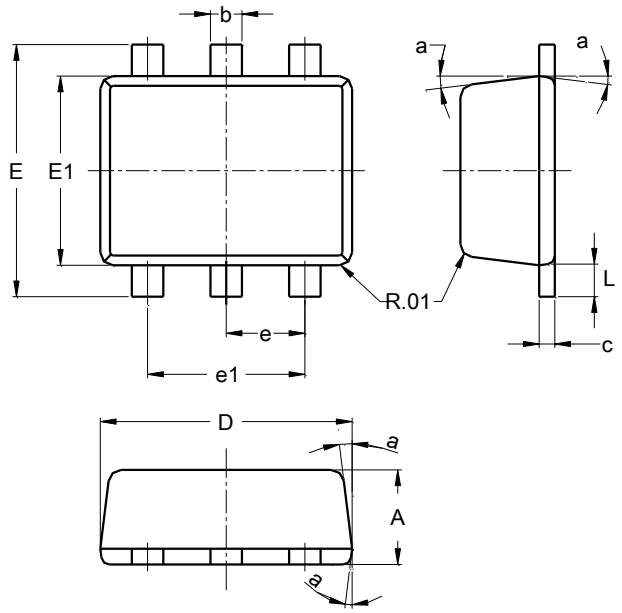
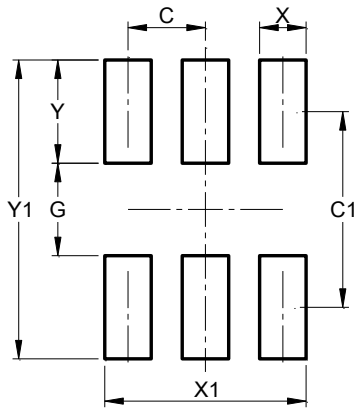


SOT563			
Dim	**Min**	**Max**	**Typ**
A	0.55	0.60	--
b	0.15	0.30	0.20
c	0.10	0.18	0.11
D	1.50	1.70	1.60
E	1.55	1.70	1.60
E1	1.10	1.25	1.20
e	--	--	0.50
e1	0.90	1.10	1.00
L	0.10	0.30	0.20
a	8°	9°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT563



Dimensions	Value (in mm)
C	0.500
C1	1.270
G	0.600
X	0.300
X1	1.300
Y	0.670
Y1	1.940

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